ABSTRACT

METHOD FOR DICING SEMICONDUCTOR WAFER

To prevent scattering of minute triangular end-material fragments from the outer-peripheral end edge of the semiconductor wafer at both a dicing step and a grinding step not to lose recognizability of the information of the ID mark and discriminability of a notch formed for indicating the crystal orientation of the semiconductor wafer, a method for dicing a semiconductor wafer formed with semiconductor chips demarcated by streets includes: at least a groove formation step of cutting and forming grooves whose depth corresponds to a finish thickness of the semiconductor chips, along the streets leaving a slight outer peripheral region of the semiconductor wafer uncut, a protective-member disposition step of disposing a protective member on the front surface of the semiconductor wafer formed with the grooves, and a splitting step of grinding a back surface of the semiconductor wafer so as to expose the grooves, thereby dicing the semiconductor wafer into the individual semiconductor chips.

Figure 6.